



60V P-Channel Enhancement Mode MOSFET

Voltage

-60 V

Current

-7 A

Features

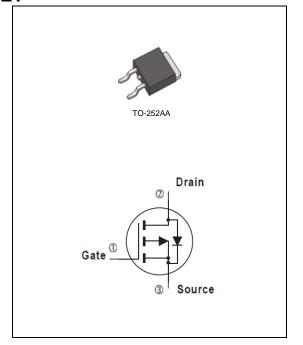
- $R_{DS(ON)}$, $V_{GS}@-10V$, $I_D@-3.5A<170m\Omega$
- $R_{DS(ON)}$, $V_{GS}@-4.5V$, $I_D@-2A<220m\Omega$
- High switching speed
- Improved dv/dt capability
- Low Gate Charge
- Low reverse transfer capacitance
- AEC-Q101 qualified
- Lead free in compliance with EU RoHS 2.0
- Green molding compound as per IEC 61249 Standard

Mechanical Data

• Case: TO-252AA Package

Terminals: Solderable per MIL-STD-750, Method 2026

• Approx. Weight: 0.0104 ounces, 0.297grams



Maximum Ratings and Thermal Characteristics (T_A=25 °C unless otherwise noted)

PARAMETER		SYMBOL	LIMIT	UNITS	
Drain-Source Voltage		V_{DS}	-60	V	
Gate-Source Voltage		V_{GS}	<u>+</u> 20	V	
Continuous Drain Current	T _C =25°C	l _D	-7.0	А	
	T _C =100°C		-4.3		
Pulsed Drain Current (Note 1)	T _C =25°C	I _{DM}	-28	<u> </u>	
Power Dissipation	T _C =25°C	Po	15.6	34/	
	T _C =100°C		6.2	W	
Continuous Drain Current	T _A =25°C	I _D	-2.5	Α	
	T _A =70°C		-2.0	Α	
Power Dissipation	T _A =25°C	-	2.0	W	
Power Dissipation	T _A =70°C	Pb	1.3		
Single Pulse Avalanche Energy (Note 6)		E _{AS}	32	mJ	
Operating Junction and Storage Temperature Range		T_J, T_{STG}	-55~150	°C	
Typical Thermal resistance (Note 4,5)	Junction to Case	$R_{ heta JC}$	8	°C/W	
	Junction to Ambient	$R_{\theta JA}$	62.5		

Limited only By Maximum Junction Temperature





Electrical Characteristics (T_A=25 °C unless otherwise noted)

PARAMETER	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNITS
Static						
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V,I _D =-250uA	-60	-	-	V
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}$, $I_{D}=-250uA$	-1.0	-1.88	-2.5	
Drain-Source On-State Resistance	R _{DS(on)}	V _{GS} =-10V,I _D =-3.5A	_	150	170	mΩ
		V _{GS} =-4.5V,I _D =-2A	-	190	220	
Zero Gate Voltage Drain Current	I _{DSS}	V_{DS} =-60V, V_{GS} =0V	-	-	-1.0	uA
Gate-Source Leakage Current	I _{GSS}	V _{GS} = <u>+</u> 20V,V _{DS} =0V	-	-	<u>+</u> 100	nA
Dynamic (Note 7)		-				
Total Gate Charge	Q_g	\/ 20\/ L 2A	-	8.3	-	nC
Gate-Source Charge	Q_gs	V_{DS} =-30V, I_{D} =-3A, V_{GS} =-10V (Note 2,3)	_	1.8	-	
Gate-Drain Charge	Q_{gd}	V _{GS} =-10 V	-	1.6	-	
Input Capacitance	Ciss		-	430	-	pF
Output Capacitance	Coss	V_{DS} =-30V, V_{GS} =0V, f =1.0MHZ	-	33	-	
Reverse Transfer Capacitance	Crss	I=1.0IVII IZ	-	29	-	
Turn-On Delay Time	td _(on)	V 20V I 4.0A	-	5.1	-	
Turn-On Rise Time	t _r	V_{DS} =-30V, I_{D} =-1.0A, V_{GS} =-10V, R_{G} =6 Ω	-	20	-	ns
Turn-Off Delay Time	td _(off)	(Note 2,3)	-	36	-	
Turn-Off Fall Time	t _f		-	11	-	
Drain-Source Diode						
Maximum Continuous Drain-Source	ı				-7	Α
Diode Forward Current	I _S		-	-	-/	A
Reverse Recovery Time	V_{SD}	I _S =-1A,V _{GS} =0V	-	-0.76	-1.0	V

NOTES:

- 1. Pulse width<a>300us, Duty cycle<a>2%
- 2. Essentially independent of operating temperature typical characteristics
- 3. Repetitive rating, pulse width limited by junction temperature TJ(MAX)=150°C. Ratings are based on low frequency and duty cycles to keep initial TJ =25°C.
- 4. The maximum current rating is package limited
- 5. Rejah is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins. Mounted on a 1 inch² with 2oz.square pad of copper
- 6. L=1mH, I_{AS} =-8A, V_{GS} =-10V, V_{DS} =-25V, R_{G} =25 ohm
- 7. Guaranteed by design, not subject to production testing.





TYPICAL CHARACTERISTIC CURVES

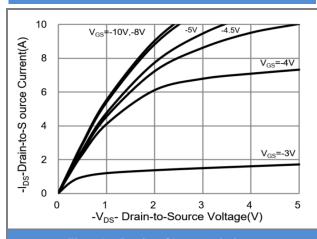


Fig.1 On-Region Characteristics

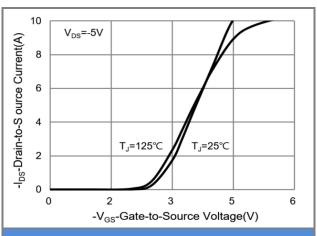


Fig.2 Transfer Characteristics

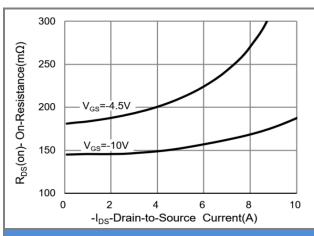


Fig.3 On-Resistance vs. Drain Current

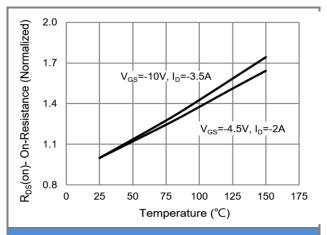
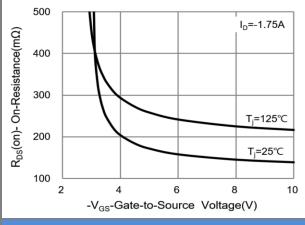


Fig.4 On-Resistance vs. Junction temperature





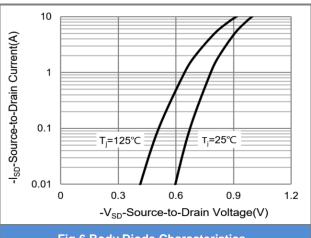


Fig.6 Body Diode Characteristics





TYPICAL CHARACTERISTIC CURVES

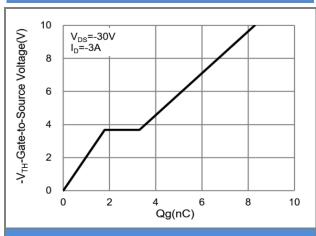


Fig.7 Gate-Charge Characteristics

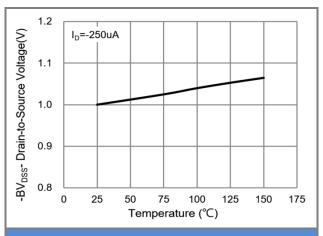


Fig.8 Breakdown Voltage Variation vs. Temperature

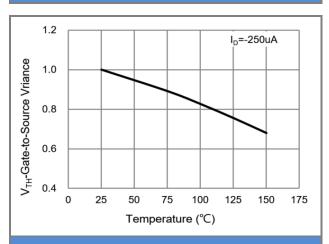


Fig.9 Threshold Voltage Variation with Temperature.

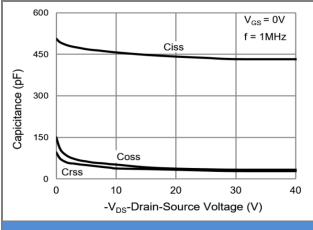


Fig.10 Capacitance vs. Drain-Source Voltage.

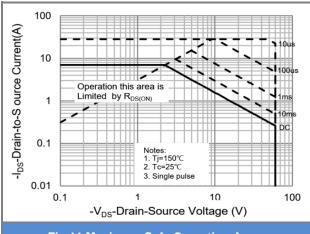


Fig.11 Maximum Safe Operating Area





TYPICAL CHARACTERISTIC CURVES

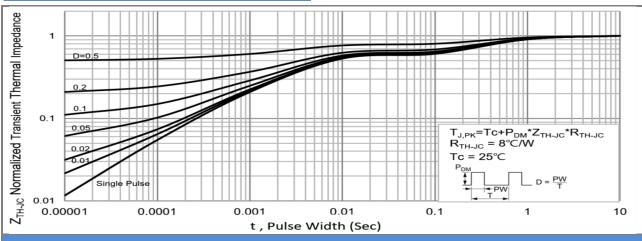


Fig.12 Normalized Thermal Transient Impedance

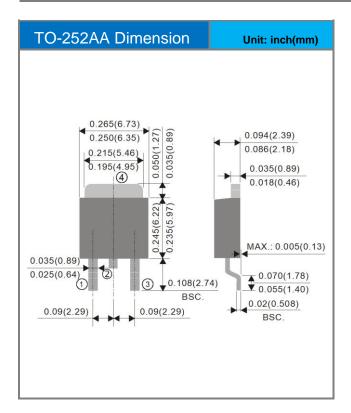


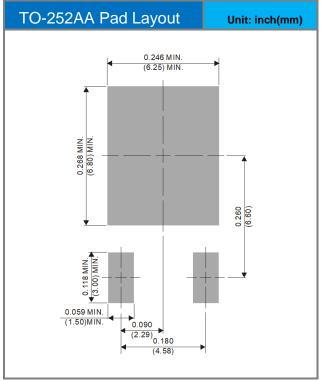


Part No Packing Code Version

Part No Packing Code	Package Type	Packing Type	Marking	Version	
PJD9P06A-AU_L2_000A1	TO-252AA	3,000pcs / 13" reel	D9P06A	Halogen free	

Packaging Information & Mounting Pad Layout









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